

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



Docket No. 0819-0703

25-02
H979

In re Patent Application of) Art Unit: Unassigned
Yoshiaki HASEGAWA et al.) Examiner: Unassigned
Serial No. 09/993,771)
Filed: November 27, 2001)
For: METHOD FOR MANUFACTURING)
SEMICONDUCTOR AND METHOD))
FOR MANUFACTURING)
SEMICONDUCTOR DEVICE)

CERTIFICATE OF MAILING

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Washington, D.C. 20231, on APR 11 2002

PRELIMINARY AMENDMENT

Honorable Commissioner of Patents
Washington, D.C. 20231

Sir:

Please preliminarily amend the above identified patent application as follows:

IN THE SPECIFICATION:

Please amend the specification as follows:

On Page 27, First Full Paragraph

Thus, according to the second variation, the etching stop layer **19C** having a super lattice structure is formed under the p-type second cladding layer **20** to be etched, whereby it is possible to control the thickness (remaining thickness) of the p-type first cladding layer **18** with a high precision. As a result, it is possible to obtain a desired thickness, i.e., an optimal value, for the thickness of the p-type first cladding layer **18**. Therefore, the light confinement efficiency in the MQW active layer **15** is significantly improved. This is because of the prevention of an etching damage to the MQW active layer **15**.

On Page 30, Fourth Paragraph continuing on Page 31

As illustrated in FIG. 10, during the etching process on the p-type second cladding layer **20**, which is made of p-type $Al_{0.07}Ga_{0.93}N$, the wavelength of the detected PL light is about 350